

AlGaAs HIGH POWER SIDE LOOK PACKAGE INFRARED EMITTING DIODE

MIE-114H4

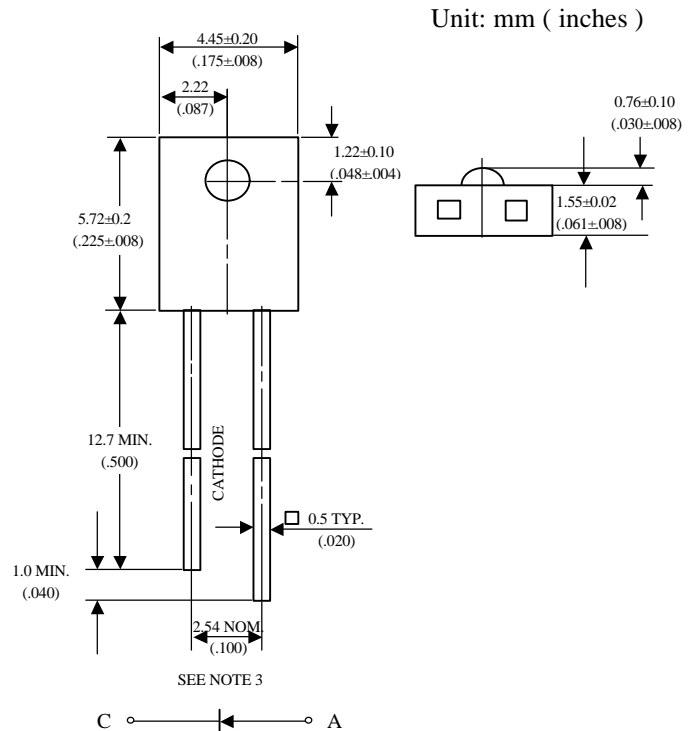
Description

The MIE-114H4 is a AlGaAs infrared emitting diode molded in clear, lensed side looking package .
The MIE-114H4 provides a broad range of intensity selection .

Features

- High power
- Mechanically and spectrally matched to the MID-11422 of phototransistor .

Package Dimensions



NOTES :

1. Tolerance is ± 0.25 mm (.010") unless otherwise noted.
2. Lead spacing is measured where the leads emerge from the package.

Absolute Maximum Ratings

@ $T_A = -25^\circ\text{C}$

Parameter	Maximum Rating	Unit
Power Dissipation	75	mW
Peak Forward Current	1	A
Continuous Forward Current	50	mA
Reverse Voltage	5	V
Operating Temperature Range	-55°C to + 100°C	
Storage Temperature Range	-55°C to + 100°C	
Lead Soldering Temperature	260°C for 5 seconds	

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Optical-Electrical Characteristics

@ T_A=25°C

Parameter	Test Conditions	Symbol	Min.	Typ .	Max.	Unit
Radiant Incidence	I _F =20mA	Ee	-	1.0	-	mW/cm ²
Forward Voltage	I _F =20mA	V _F	-	1.5	1.6	V
Reverse Current	V _R =5V	I _R	-	-	100	μA
Peak Wavelength	I _F =20mA	λ _p	-	850	-	nm
Spectral Bandwidth	I _F =20mA	Δλ	-	30	-	nm
View Angle	I _F =20mA	2θ _{1/2}	-	80	-	deg .

Typical Optical-Electrical Characteristic Curves

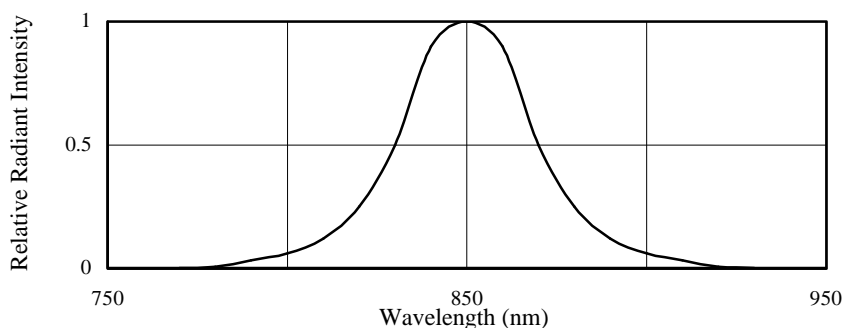


FIG.1 SPECTRAL DISTRIBUTION

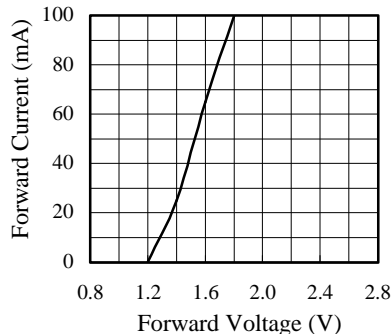


FIG.2 FORWARD CURRENT VS. FORWARD VOLTAGE

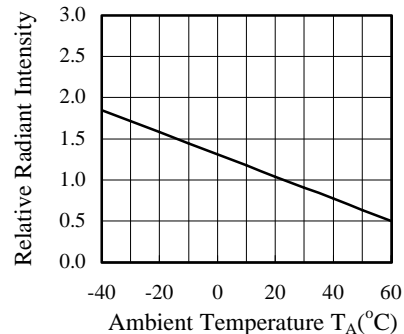


FIG.3 RELATIVE RADIANT INTENSITY VS. AMBIENT TEMPERATURE

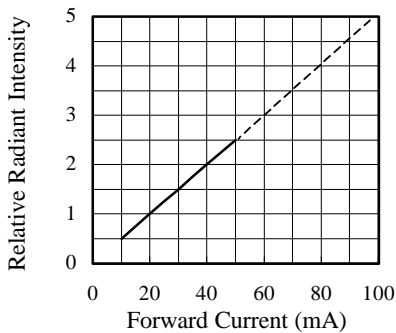


FIG.4 RELATIVE RADIANT INTENSITY VS. FORWARD CURRENT

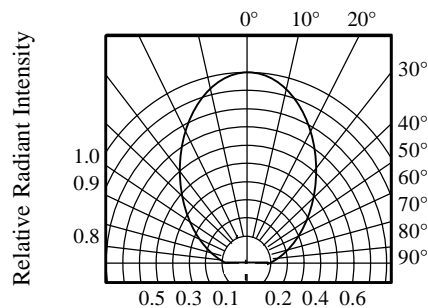


FIG.5 RADIATION DIAGRAM